

STP45NF3LL - STP45NF3LLFP STB45NF3LL

N-channel 30V - 0.014Ω - 45A TO-220 - TO-220FP - D²PAK STripFET II™ power MOSFET

General features

Туре	V _{DSS}	R _{DS(on)}	I _D
STB45NF3LL	30V	<0.018Ω	45A
STP45NF3LLFP	30V	<0.018Ω	45A
STP45NF3LL	30V	<0.018Ω	27A

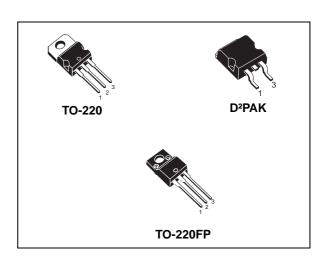
- Optimal R_{DS(on)} x Q_g trade-off @ 4.5V
- Conduction losses reduced
- Switching losses reduced

Description

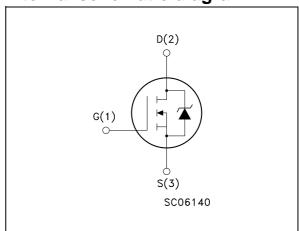
This application specific Power MOSFET is the third genaration of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows the best trade-off between on-resistance ang gate charge. When used as high and low side in buck regulators, it gives the best performance in terms of both conduction and switching losses. This is extremely important for motherboards where fast switching and high efficiency are of paramount importance.

Applications

Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STB11NM60FD	B11NM60FD	D²PAK	Tape & reel
STB11NM60FD-1	B11NM60FD	I ² PAK	Tube
STP11NM60FD	P11NM60FD	TO-220	Tube

August 2006 Rev 4 1/16

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1 Electrical ratings

Table 1. Absolute maximum ratings

		Val	Unit	
Symbol	Parameter	TO-220/ D²PAK/I²PAK	TO-220FP	
V _{DS}	Drain-source voltage (v _{gs} = 0)	30)	V
V_{DGR}	Drain-gate voltage (R_{GS} = 20 kΩ)	30)	V
V_{GS}	Gate- source voltage	±1	V	
I _D	Drain current (continuos) at T _C = 25°C	5°C 45		Α
I _D	Drain current (continuos) at T _C = 100°C	32	19	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	180	108	Α
P _{TOT}	Total dissipation at T _C = 25°C	70	25	W
	Derating factor	0.46	0.167	W/°C
E _{AS} (2)	Single pulse avalanche energy	241		mj
V _{ISO}	Insulation winthstand voltage (dc)	2500		V
T _{stg}	Storage temperature	– 55 to	°C	
T _j	Max. operating junction temperature	- 55 10		

^{1.} Pulse width limited by safe operating area

Table 2. Thermal data

		Val			
Symbol	Parameter	TO-220 D²PAK	TO-220FP	Unit	
R _{thj-case}	Thermal resistance junction-case Max	2.14	6	°C/W	
R _{thj-a}	Thermal resistance junction-ambient Max	62	°C/W		
T _I	Maximum lead temperature for soldering purpose	30	°C		

^{2.} Starting T_j = 25°C, I_D = 22.5A, V_{DD} = 24V

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0$	30			V
	Zero gate voltage	V _{DS} = Max rating			1	μA
I _{DSS}	Drain current (V _{GS} = 0)	V _{DS} =Max rating, T _C =125°C			10	μΑ
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ±16V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1			V
R _{DS(on)}	Static drain-source on resistance	$V_{GS} = 10V, I_D = 22.5A$ $V_{GS} = 4.5V, I_D = 22.5A$		0.014 0.016	0.018 0.020	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions Min.		Тур.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	$V_{DS} = 15V_{,} I_{D} = 22.5A$		20		S
C _{iss}	Input capacitance			800		pF
C _{oss}	Output capacitance	$V_{DS} = 25V, f = 1 MHz,$ $V_{GS} = 0$		250		pF
C _{rss}	Reverse transfer capacitance	$V_{GS} = 0$		60		pF
Qg	Total gate charge	., .,,		12.5	17	nC
Q_{gs}	Gate-source charge	$V_{DD} = 24V, I_D = 45A,$ $V_{GS} = 5V$		4.6		nC
Q_{gd}	Gate-drain charge	*GS - 0 v		5.2		nC

^{1.} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Table 5. Switching times

	Curitoning unioc					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time Rise time	$V_{DD} = 15V, I_{D} = 22.5A$ $R_{G} = 4.7\Omega V_{GS} = 4.5V$ (see Figure 15)		17 100		ns ns
t _{d(off)}	Turn-off-delay time Fall time	$V_{DD} = 15V, I_D = 22.5A,$ $R_G = 4.7\Omega, V_{GS} = 4.5V$ (see Figure 15)		20 21		ns ns

Table 6. Source drain diode

Symbol	Parameter Test conditions Min Ty		Тур.	Max	Unit	
I _{SD}	Source-drain current				45	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)				180	Α
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 45A, V _{GS} = 0			1.3	V
t _{rr}	Reverse recovery time	I _{SD} = 45A, V _{DD} = 15V		35		ns
Q_{rr}	Reverse recovery charge	di/dt = 100A/μs,		44		nC
I _{RRM}	Reverse recovery current	(see Figure 17)		2.5		Α

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220/ D²PAK

Figure 2. Thermal impedance for TO-220/ D²PAK

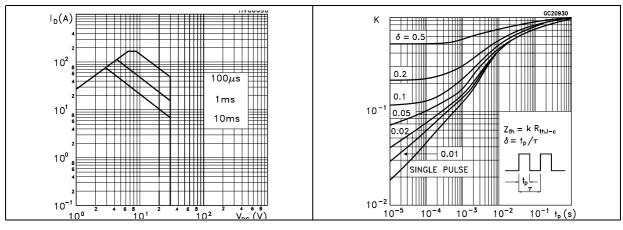


Figure 3. Safe operating areafor TO-220FP

Figure 4. Thermal impedance for TO-220FP

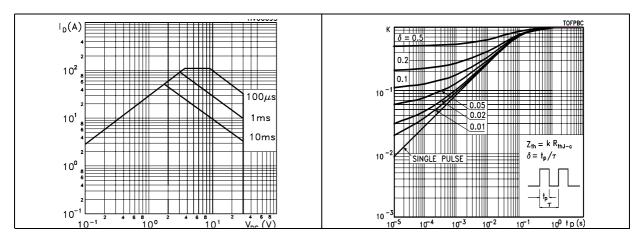


Figure 5. Output characterisics

Figure 6. Transfer characteristics

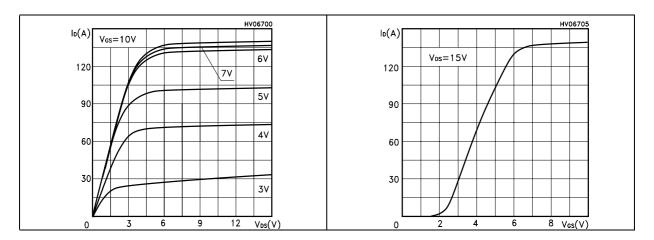


Figure 7. Transconductance

Figure 8. Static drain-source on resistance

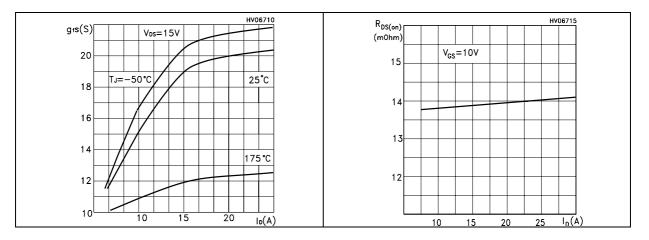


Figure 9. Gate charge vs gate-source voltage Figure 10. Capacitance variations

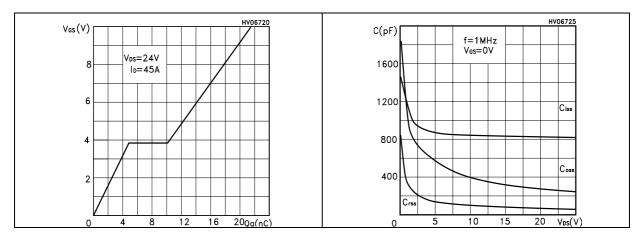


Figure 11. Normalized gate threshold voltage Figure 12. Normalized on resistance vs vs temperature temperature

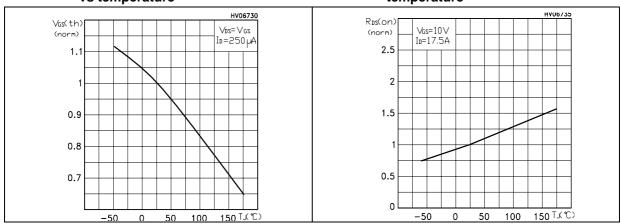
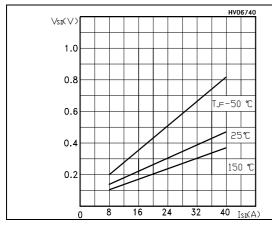
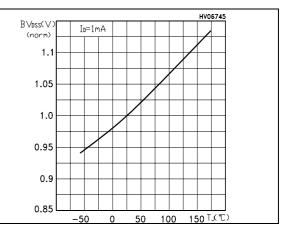


Figure 13. Source-drain diode forward characteristics

Figure 14. Normalized breakdown voltage vs tj





3 Test circuit

Figure 15. Switching times test circuit for resistive load

Figure 16. Gate charge test circuit

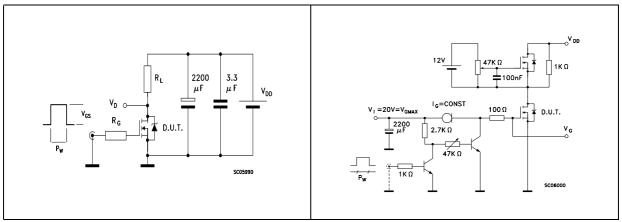


Figure 17. Test circuit for inductive load switching and diode recovery times

Figure 18. Unclamped Inductive load test circuit

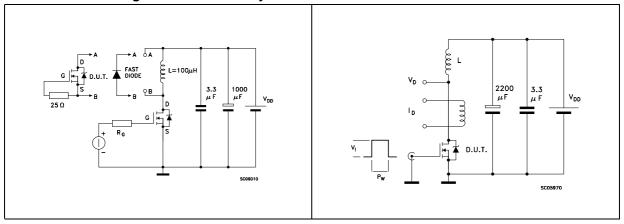
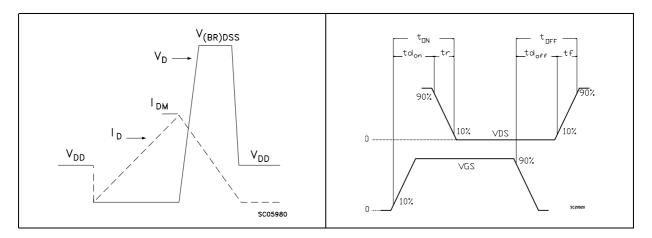


Figure 19. Unclamped inductive waveform

Figure 20. Switching time waveform



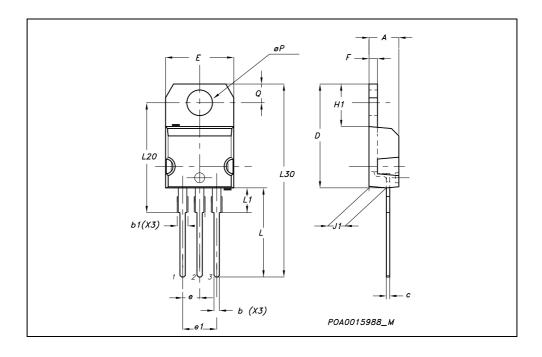
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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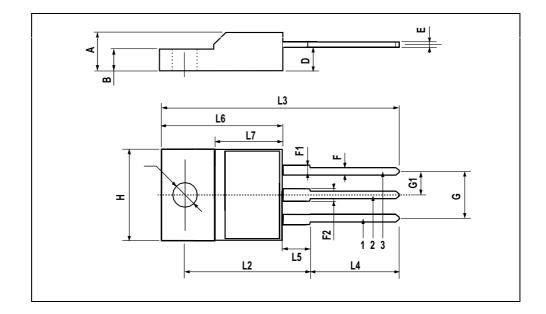
TO-220 MECHANICAL DATA

DIM.		mm.			inch	
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øΡ	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



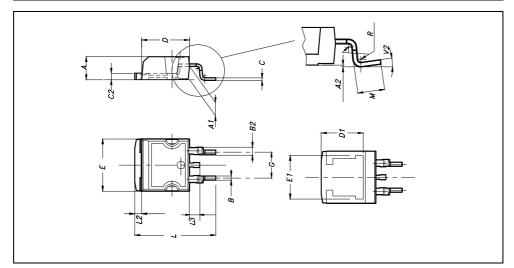
TO-220FP MECHANICAL DATA

DIM.		mm.			inch	
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



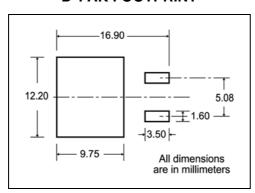
D²PAK MECHANICAL DATA

DIM.		mm.			inch	
DIW.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	O _ō		4º			

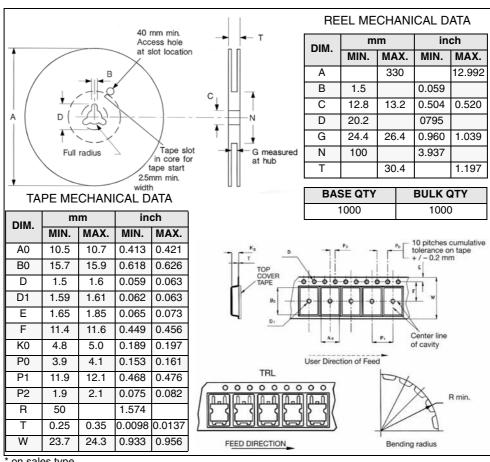


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D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



on sales type

6 Revision history

Table 7. Revision history

Date	Revision	Changes
09-Sep-2004	3	Complete document
09-Aug-2006	4	New template, no content change

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